

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	21	"5798534"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/17 14:19
S2	5	"2004028249"	EPO; JPO; DERWENT	ADJ	ON	2008/10/17 14:30
S9	2360768	memory	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/17 14:33
S10	5361	(insulat\$5 state)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/17 14:33
S11	154622	TFT or (thin film transistor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/17 14:34
S12	58	S9 and S10 and S11	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/17 14:34
S13	13490	top gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/17 14:35
S14	6071	S11 and S13	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/17 14:36

S15	11	S12 and S14	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/17 14:36
S16	1968	S11 and S13 and S9	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/17 14:47
S17	385	(semiconductor (film or layer)) same (alter or change) same ((phase or state) with (voltage or current or resistance) )	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/17 14:49
S18	7	S16 and S17	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/17 14:50
S21	4	"2003036684"	EPO; JPO; DERWENT	ADJ	ON	2008/10/17 15:33
S22	2	"20020196659"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/17 15:35
S23	7098	(insulating substrate) and S9	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/17 15:36
S24	394	S23 and ((phase change) or PCM or GST or chalcogenide or (resistive material))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/17 15:38
S25	391978	(word and bit)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/17 15:42

S26	108	S24 and S25	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/17 15:42
S27	1277	(memory cell) and (insulating substrate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/17 16:05
S29	133	S27 and ((phase change) or PCM or GST or chalcogenide or (resistive material))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/17 16:09
S31	2449	S11 and ((phase change) or PCM or GST or chalcogenide or (resistive material))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/17 16:39
S32	2076	S31 and substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/17 16:41
S33	1286	(impurity or (source and drain)) and S32	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/17 16:42
S34	8047	((one time program\$5) or OTP)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/17 17:11
S35	5645	S34 and S9	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/17 17:11

S36	60	(insulating substrate) and S35	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/17 17:12
S40	14415	((write with once with memory) or (OTP) or (one time program\$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/22 18:25
S41	154822	TFT or (thin film transistor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/22 18:26
S42	417	S40 and S41	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/22 18:26
S43	60	island AND S42	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/22 18:44
S44	33	("20020008278"   "20020089024"   "20020089024"   "20020105050"   "20020141221"   "20020149468"   "20030146467"   "20050140501"   "20050212662"   "4092524"   "4092524"   "4152627"   "6005270"   "6005270"   "6317028"   "6583490"   "6625057"   "6800527"   "6933848"   "7164611").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/22 19:28
S45	154941	TFT or (thin film transistor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/23 09:00

S46	336	(fuse with memory) and S45	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/23 09:00
S47	34	("20010026187"   "20030183699"   "20040150468"   "20040164302"   "20050130389"   "20050157529"   "20050170270"   "20050180187"   "20060054707"   "20070171693"   "4922319"   "5523974"   "5736728"   "6190951"   "6525595"   "6787806"   "6809952"   "6954084").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/23 10:51
S48	2	"20040164302"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/23 10:56
S49	127	257/16	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/23 11:00
S50	464	257/49	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/23 11:00
S51	557	257/52	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/23 11:00
S52	4808	257/59	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/23 11:00

S53	763	257/64	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/23 11:00
S54	575	257/68	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/23 11:00
S55	3323	(257/70-72).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/10/23 11:01
S56	2481	438/166	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/23 11:02
S57	679	438/153	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/23 11:02
S58	1553	438/478	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/23 11:02
S59	2698	(438/238-239).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/10/23 11:03

10/23/2008 11:05:46 AM

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